

N 通道 NexFET™ 功率金属氧化物半导体场效应晶体管(MOSFET)

查询样品: CSD16415Q5

特性

- 超低栅极电荷(Qg)和栅漏电荷(Qgd)
- 极低接通电阻
- 低热阻性
- 额定雪崩能量
- 无铅端子电镀
- 符合 RoHS 标准
- 无卤素

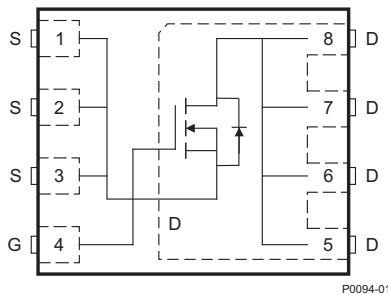
应用范围

- 负载点同步降压转换器用于网络, 电信和计算系统
- 为同步场效应晶体管(FET)应用进行了优化

说明

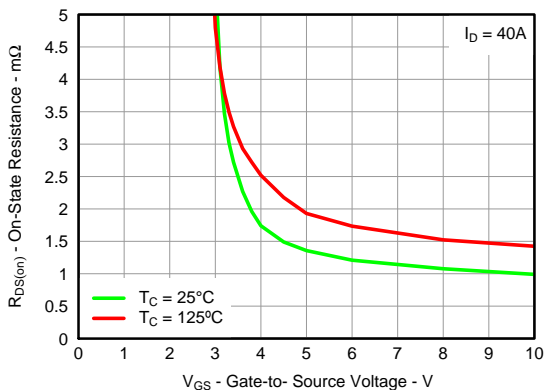
此 NexFET™ 功率MOSFET已被设计成在功率转换应用中大大降低功率损失。

顶视图



P0094-01

$r_{DS(on)}$ 对 V_{GS}



产品概述

V_{DS}	漏源极电压	25	V
Q_g	栅极电荷, 总数(4.5V)	21	nC
Q_{gd}	栅极电荷, 栅漏	5.2	nC
$r_{DS(接通)}$	漏源极接通电阻	$V_{GS} = 4.5 V$	1.5 mΩ
		$V_{GS} = 10 V$	0.99 mΩ
$V_{GS(th)}$	阈值电压	1.5	V

订购信息

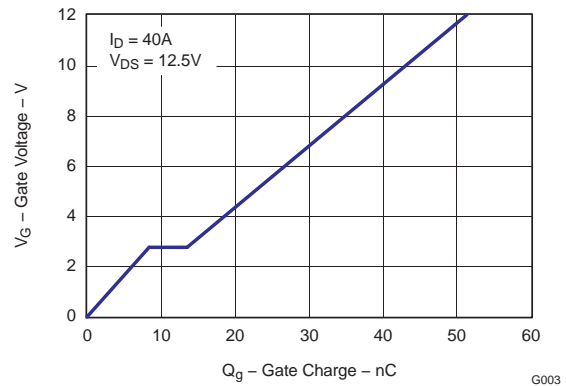
器件	封装	介质	数量	出货
CSD16415Q5	无引线小外形尺寸(SON)5mm x 6mm塑料封装	13英寸(33cm)卷带	2500	卷带

最大绝对额定值

除非另外说明, 否则 $T_A = 25^\circ C$		数值	单位
V_{DS}	漏源极电压	25	V
V_{GS}	栅源极电压	+16/-12	V
I_D	持续漏极电流, $T_C = 25^\circ C$	100	A
	持续漏极电流 ⁽¹⁾	38	A
I_{DM}	脉冲漏极电流, $T_A = 25^\circ C$ ⁽²⁾	200	A
P_D	功率耗散 ⁽¹⁾	3.2	W
T_J, T_{STG}	运行结温和存储温度范围	-55 至 150	$^\circ C$
E_{AS}	雪崩能量, 单一脉冲 $I_D = 100A, L = 0.1mH, R_G = 25 \Omega$	500	mJ

- (1) $R_{\theta JA} = 40^\circ C/W$, 此条件是在1in² (6.45cm²) Cu [2 oz. (厚度为0.071mm)] 的0.060英寸厚度为(1.52mm) FR4 印刷电路板(PCB)上。
- (2) 脉冲持续时间 $\leq 300 \mu s$, 占空比 $\leq 2\%$

栅极电荷



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain-to-source voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	25			V
I_{DSS}	Drain-to-source leakage current	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}$			1	μA
I_{GSS}	Gate-to-source leakage current	$V_{DS} = 0\text{ V}, V_{GS} = -12\text{ V to } 16\text{ V}$			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.2	1.5	1.9	V
$r_{DS(on)}$	Drain-to-source on-resistance	$V_{GS} = 4.5\text{ V}, I_D = 40\text{ A}$		1.5	1.8	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		0.99	1.15	$\text{m}\Omega$
g_{fs}	Transconductance	$V_{DS} = 15\text{ V}, I_D = 40\text{ A}$		168		S
Dynamic Characteristics						
C_{ISS}	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 12.5\text{ V}, f = 1\text{ MHz}$		3150	4100	pF
C_{OSS}	Output capacitance			2530	3300	pF
C_{RSS}	Reverse transfer capacitance			175	230	pF
R_g	Series gate resistance			1.2	2.4	Ω
Q_g	Gate charge total (4.5 V)	$V_{DS} = 12.5\text{ V}, I_D = 40\text{ A}$		21	29	nC
Q_{gd}	Gate charge, gate-to-drain			5.2		nC
Q_{gs}	Gate charge, gate-to-source			8.3		nC
$Q_{g(th)}$	Gate charge at V_{th}			4.8		nC
Q_{OSS}	Output charge	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$		55		nC
$t_{d(on)}$	Turnon delay time	$V_{DS} = 12.5\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 40\text{ A}$ $R_G = 2\ \Omega$		16.6		ns
t_r	Rise time			30		ns
$t_{d(off)}$	Turnoff delay time			20		ns
t_f	Fall time			12.7		ns
Diode Characteristics						
V_{SD}	Diode forward voltage	$I_S = 40\text{ A}, V_{GS} = 0\text{ V}$	0.85		1	V
Q_{rr}	Reverse recovery charge	$V_{DD} = 15\text{ V}, I_F = 40\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		72		nC
t_{rr}	Reverse recovery time	$V_{DD} = 15\text{ V}, I_F = 40\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		45		ns

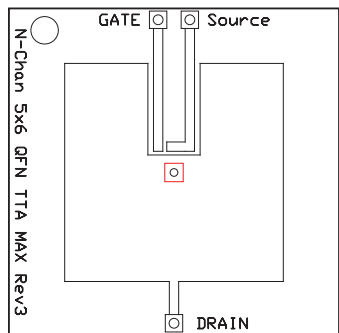
THERMAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise stated)

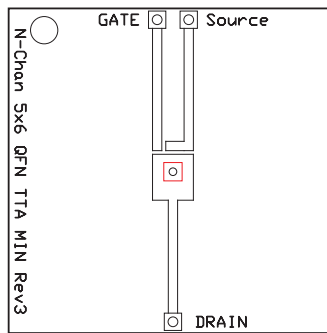
PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal resistance, junction-to-case ⁽¹⁾			1.1	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal resistance, junction-to-ambient ^{(1) (2)}			50	$^\circ\text{C}/\text{W}$

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch (2.54-cm) square, 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch \times 1.5-inch (3.81-cm \times 3.81-cm), 0.060-inch (1.52-mm) thick FR4 board. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.

(2) Device mounted on FR4 material with 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on 1
 inch^2 (6.45 cm^2) of
2-oz. (0.071-mm thick)
Cu.



Max $R_{\theta JA} = 121^{\circ}\text{C/W}$
when mounted on
minimum pad area of
2-oz. (0.071-mm thick)
Cu.

TYPICAL MOSFET CHARACTERISTICS

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)

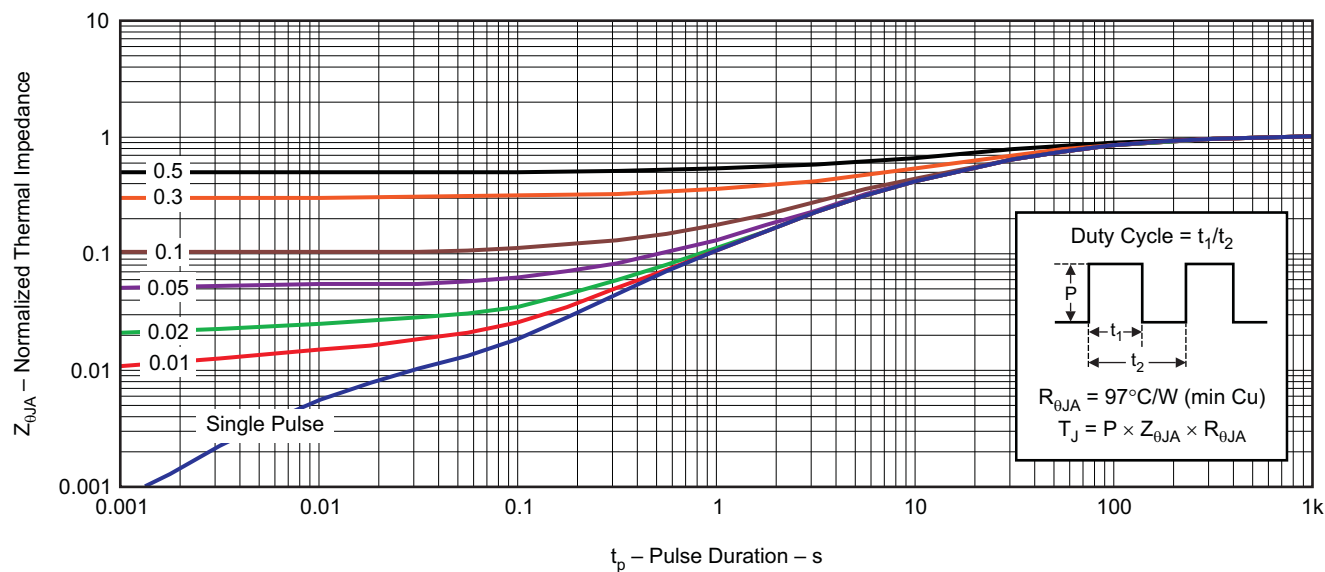


Figure 1. Transient Thermal Impedance

G012

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

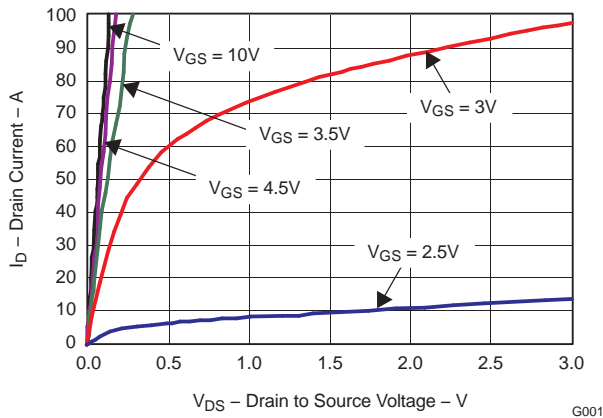


Figure 2. Saturation Characteristics

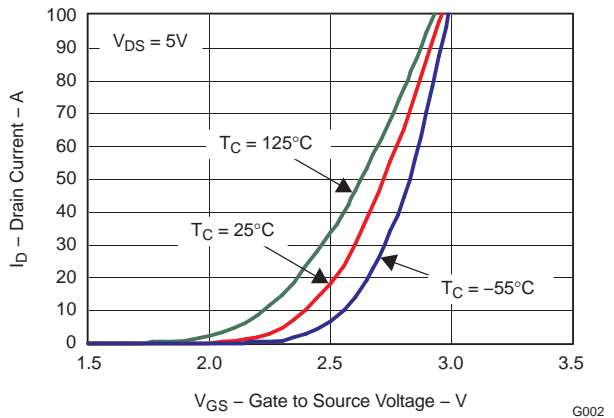


Figure 3. Transfer Characteristics

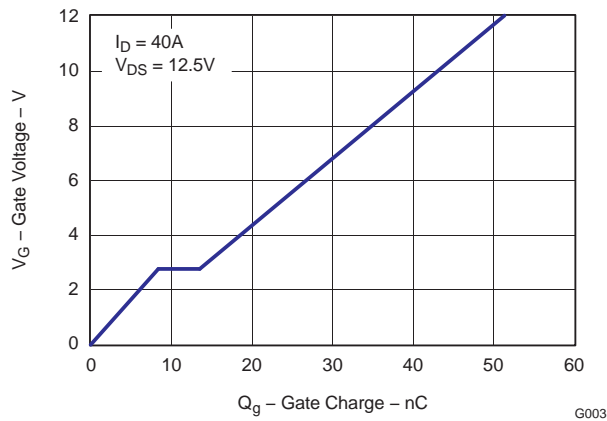


Figure 4. Gate Charge

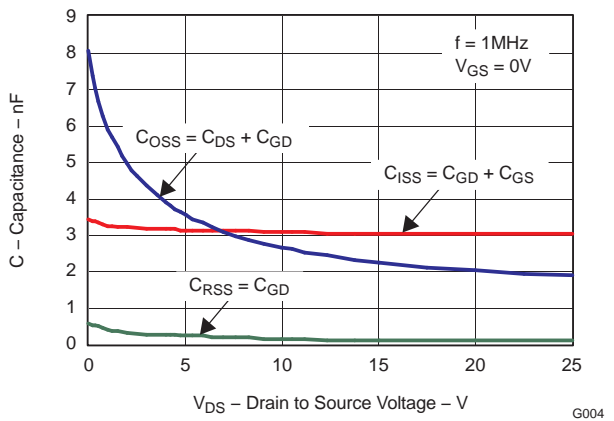


Figure 5. Capacitance

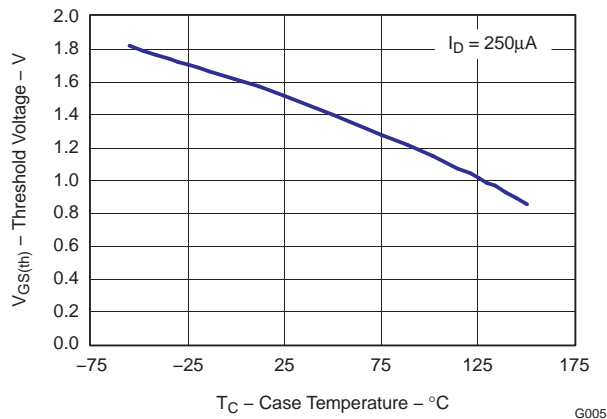


Figure 6. Threshold Voltage vs. Temperature

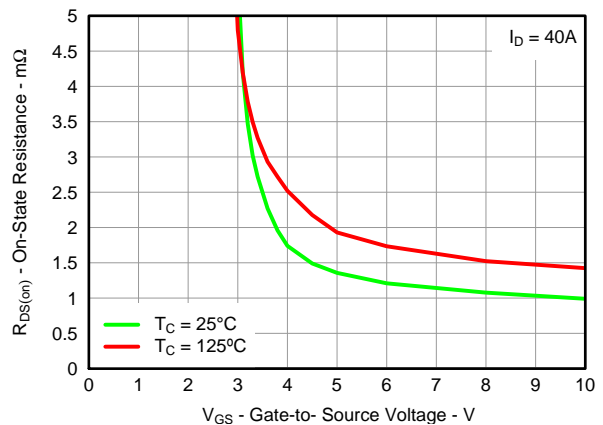


Figure 7. On-Resistance vs. Gate Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

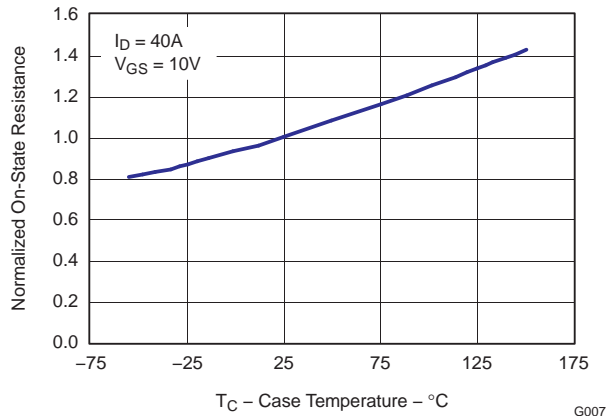


Figure 8. On-Resistance vs. Temperature

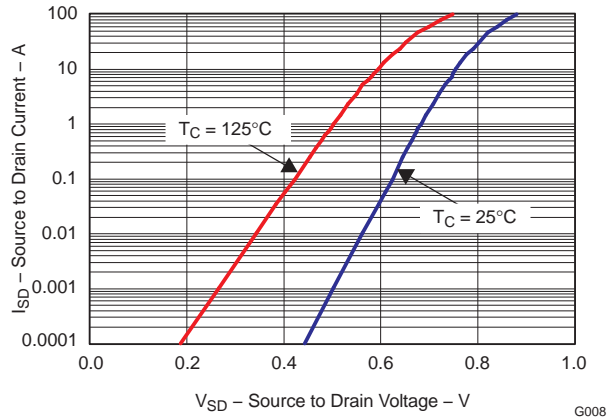


Figure 9. Typical Diode Forward Voltage

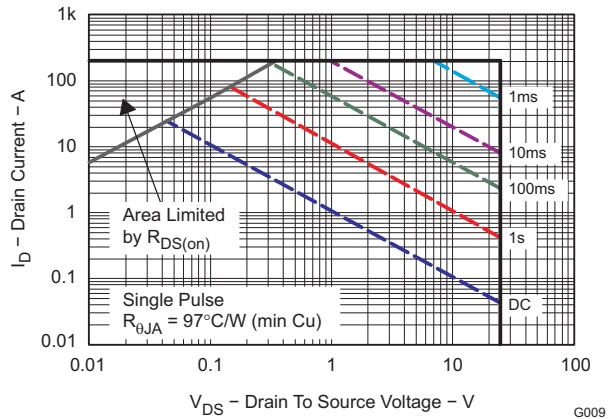


Figure 10. Maximum Safe Operating Area

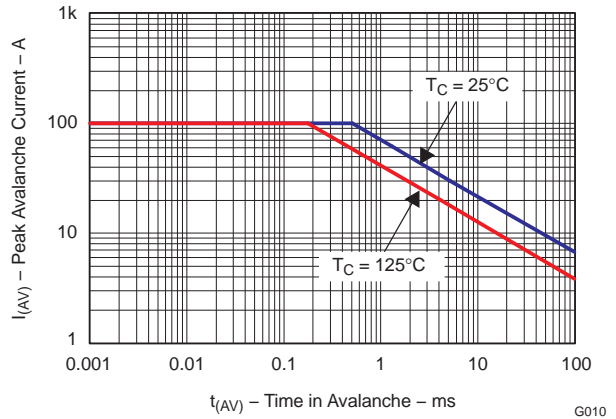


Figure 11. Single-Pulse Unclamped Inductive Switching

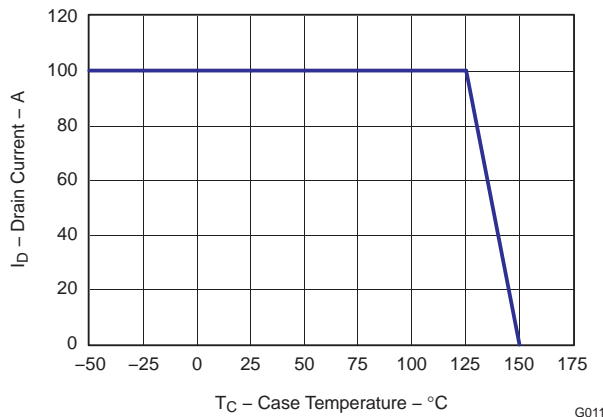
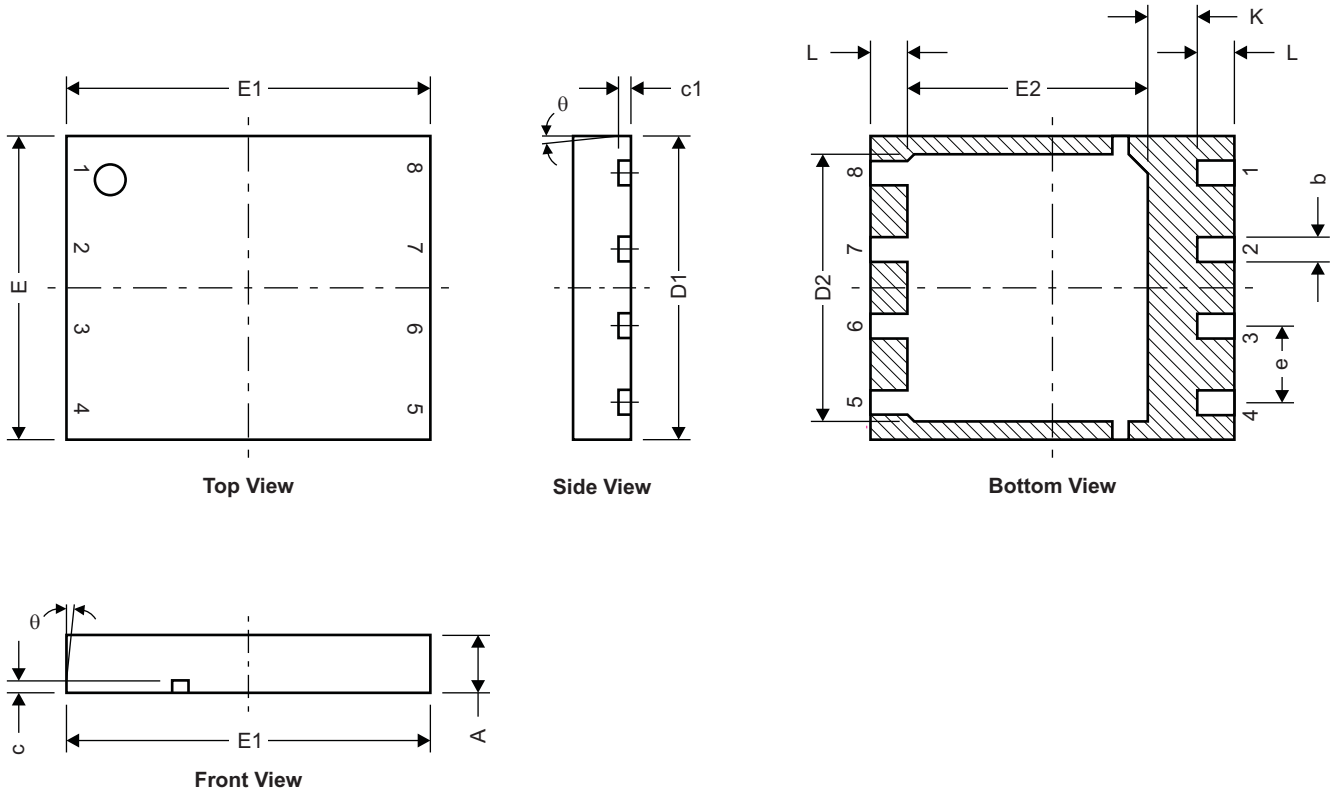


Figure 12. Maximum Drain Current vs. Temperature

MECHANICAL DATA

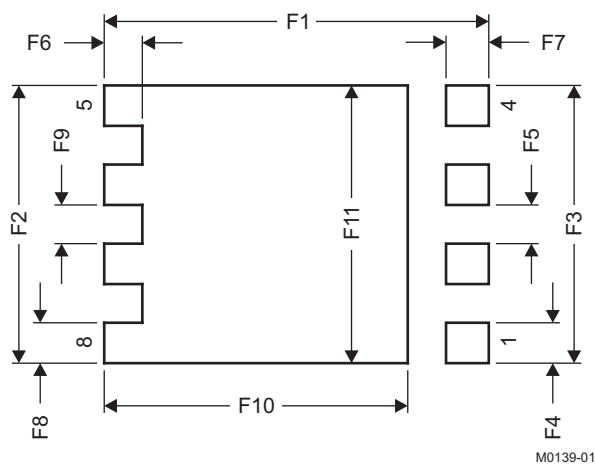
Q5 Package Dimensions



M0140-01

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00			

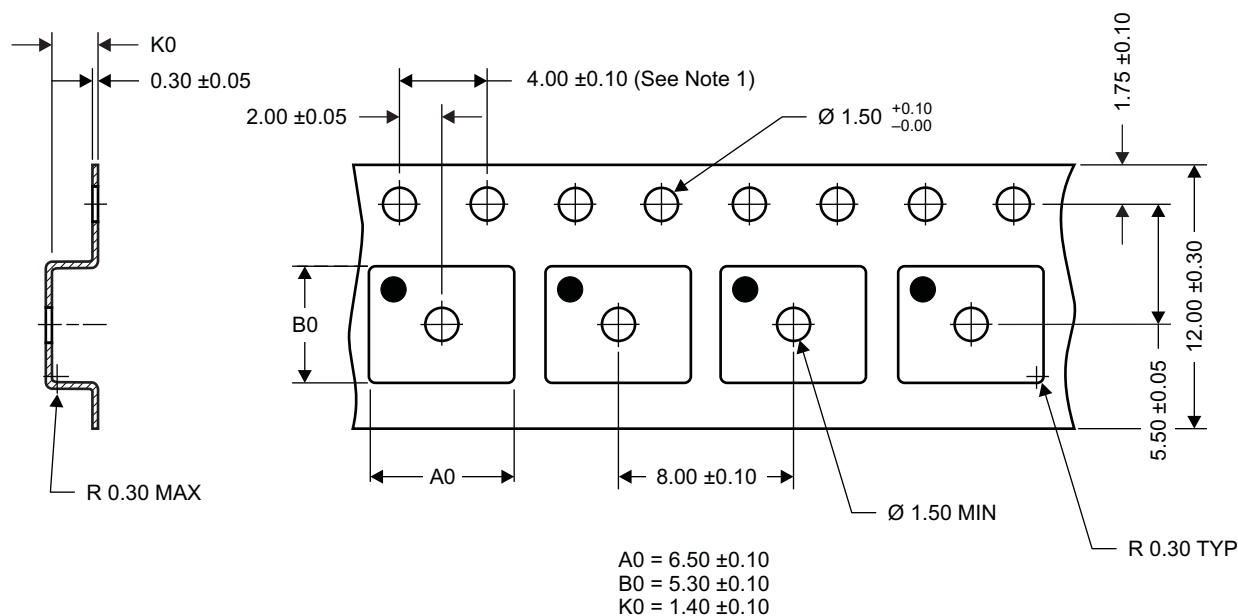
Figure 13. Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note [SLPA005](#) – *Reducing Ringing Through PCB Layout Techniques*.

Q5 Tape and Reel Information



M0138-01

Notes:

- 10 sprocket hole pitch cumulative tolerance ± 0.2
- Camber not to exceed 1 mm IN 100 mm, noncumulative over 250 mm
- Material: black static dissipative polystyrene
- All dimensions are in mm (unless otherwise specified)
- A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket
- MSL1 260°C (IR and Convection) PbF Reflow Compatible

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD16415Q5	Active	Production	VSON-CLIP (DQH) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16415
CSD16415Q5.B	Active	Production	VSON-CLIP (DQH) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16415
CSD16415Q5T	Active	Production	VSON-CLIP (DQH) 8	250 SMALL T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16415
CSD16415Q5T.B	Active	Production	VSON-CLIP (DQH) 8	250 SMALL T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD16415

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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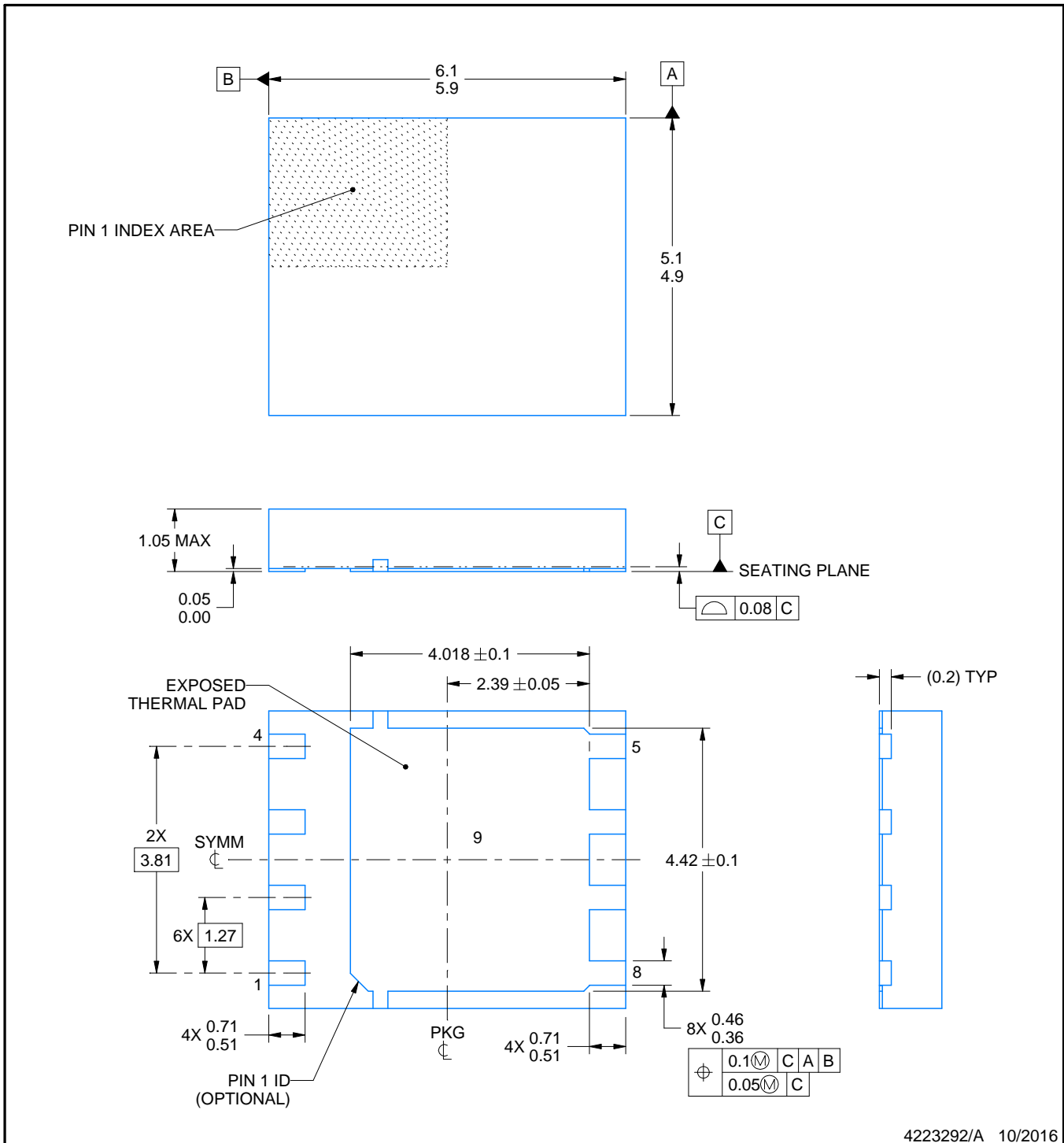
DQH0008A



PACKAGE OUTLINE

VSON-CLIP - 1.05 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



4223292/A 10/2016

NOTES:

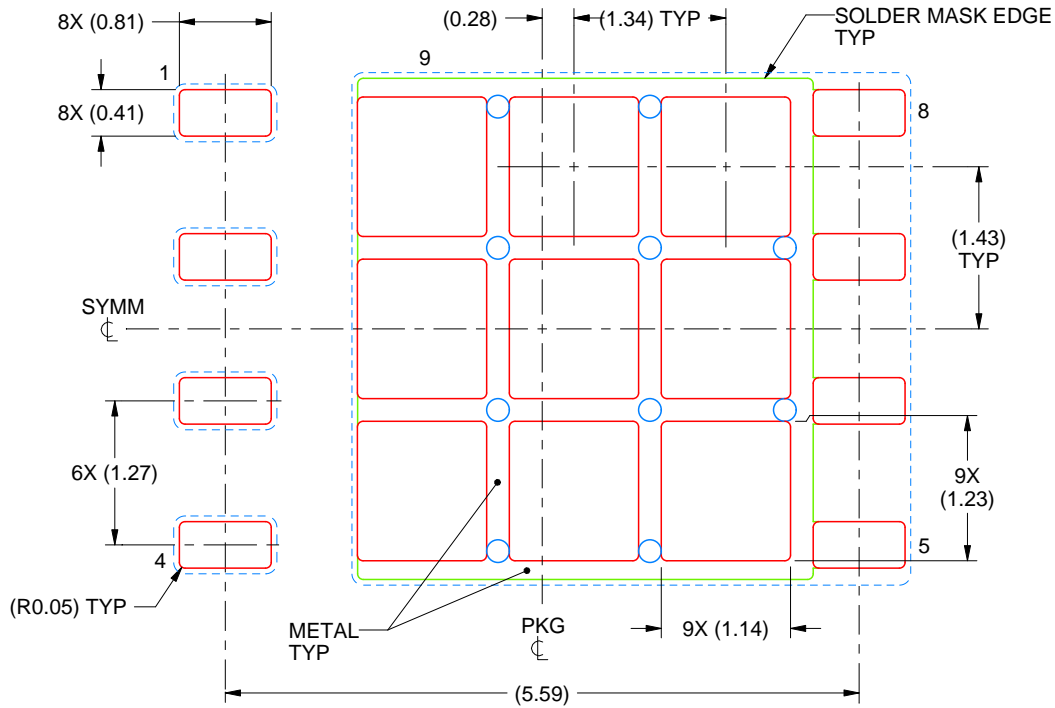
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE STENCIL DESIGN

DQH0008A

VSON-CLIP - 1.05 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:
71% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:15X

4223292/A 10/2016

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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最后更新日期：2025 年 10 月